DGG OR DL PACKAGE

(TOP VIEW)

- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

NOTE: For order entry:

The DGG package is abbreviated to G.

description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 1.65-V to 3.6-V $\rm V_{CC}$ operation.

The SN74ALVCHR162245 is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable (OE) input can be used to disable the device so that the buses are effectively isolated.

All outputs, which are designed to sink up to 12 mA, include equivalent 26- Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCHR162245 is characterized for operation from -40°C to 85°C.

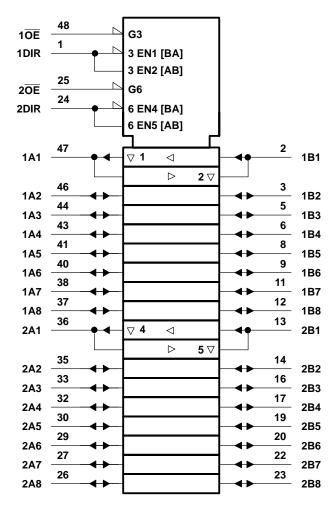
1DIR L 1B1 📙 2 47 1 1A1 46 1 1A2 1B2 | 3 GND L 4 45 GND 1B3 🛮 5 44 🛮 1A3 1B4 🛮 6 43 1 1A4 42 V_{CC} V_{CC} **Ц** 7 1B5 🛮 8 41 1 1A5 1B6 🛮 9 40 L 1A6 39 GND GND | 10 1B7 [11 38 🛮 1A7 1B8 🛮 12 37 L 1A8 2B1 13 36 2A1 2B2 1 14 35 2A2 GND II 15 34 II GND 2B3 16 33 2A3 2B4 🛮 17 32 D 2A4 V_{CC} **Ц** 18 31 V_{CC} 2B5 [] 19 30 2A5 2B6 20 29 2A6 GND 21 28 GND 2B7 🛮 22 27 2A7 2B8 🛮 23 26 2A8 25 20E 2DIR | 24

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FUNCTION TABLE (each 8-bit section)

INP	UTS	OPERATION			
OE	DIR	OPERATION			
L	L	B data to A bus			
L	Н	A data to B bus			
Н	Χ	Isolation			

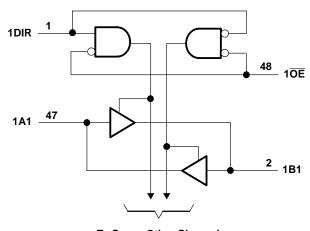
logic symbol†

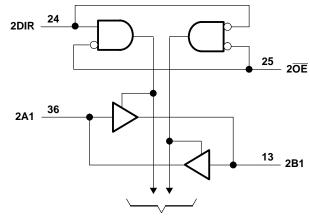


[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)





To Seven Other Channels

To Seven Other Channels

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I : Except I/O ports (see Note 1)	
I/O ports (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Output voltage range, V _O (see Notes 1 and 2)	
Input clamp current, $I_{ K }(V_{ } < 0)$	
Output clamp current, I _{OK} (V _O < 0)	−50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	e 89°C/W
DL package	94°C/W
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
VCC	Supply voltage	1.65	3.6	V		
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		ı	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$		
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		
VI	Input voltage		0	Vcc	V	
٧o	Output voltage		0	Vcc	V	
		V _{CC} = 1.65 V		-2		
1	High-level output current	V _{CC} = 2.3 V		-6	mA	
ЮН		V _{CC} = 2.7 V		-8		
		V _{CC} = 3 V		-12		
		V _{CC} = 1.65 V		2		
lOL	Lave lavel autout august	V _{CC} = 2.3 V		6	A	
	Low-level output current	V _{CC} = 2.7 V	8		mA	
	V _{CC} = 3 V			12		
Δt/Δν	Input transition rise or fall rate			10	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAI	RAMETER	TEST CO	ONDITIONS	Vcc	MIN	TYP†	MAX	UNIT	
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	2			
		$I_{OH} = -2 \text{ mA}$		1.65 V	1.2				
		I _{OH} = -4 mA	2.3 V	1.9					
Voн		I _{OH} = -6 mA		2.3 V	1.7			V	
		IOH = -0 IIIA		3 V	2.4				
		I _{OH} = -8 mA		2.7 V	2				
		I _{OH} = -12 mA		3 V	2				
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
		$I_{OL} = 2 \text{ mA}$	1.65 V			0.45			
	I _{OL} = 4 mA		2.3 V			0.4			
VOL		J		2.3 V			0.55	V	
	I _{OL} = 6 mA	3 V			0.55				
	I _{OL} = 8 mA	2.7 V			0.6				
II		I _{OL} = 12 mA	3 V			0.8			
Ц		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ	
		V _I = 0.58 V		1.65 V	25				
		V _I = 1.07 V		1.03 V	-25				
		V _I = 0.7 V		2.3 V	45				
I	V _I = 1.7 V		2.5 V	-45			μА		
		V _I = 0.8 V		3 V	75				
		V _I = 2 V			-75				
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500		
loz§		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ	
ICC		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
ΔlCC		One input at V_{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ	
Ci	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		4		pF	
C _{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		9		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} = 2.5 V ± 0.2 V				V _{CC} = 3.3 V ± 0.3 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	B or A	¶	1	4.9		4.7	1	4.2	ns
^t en	ŌĒ	B or A	¶	1	6.8		6.7	1	5.6	ns
^t dis	ŌĒ	B or A	¶	1	6.3		5.7	1	5.5	ns

 $[\]P$ This information was not available at the time of publication.



[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

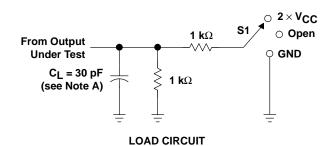
 $[\]mbox{\$}$ For I/O ports, the parameter $\mbox{I}_{\mbox{OZ}}$ includes the input leakage current.

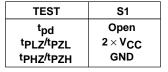
operating characteristics, $T_A = 25^{\circ}C$

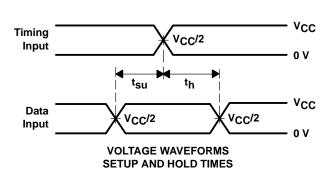
PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT	
		TEST CONDITIONS	TYP	TYP	TYP	UNIT	
	Power dissipation	Outputs enabled	C _I = 50 pF, f = 10 MHz	†	24	32	pF
Cpd	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	4	5	рг

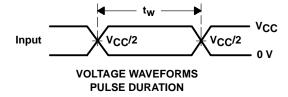
[†] This information was not available at the time of publication.

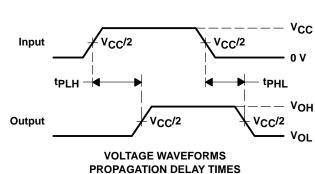
PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V}$

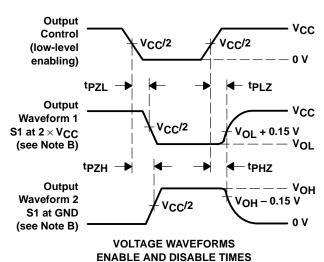












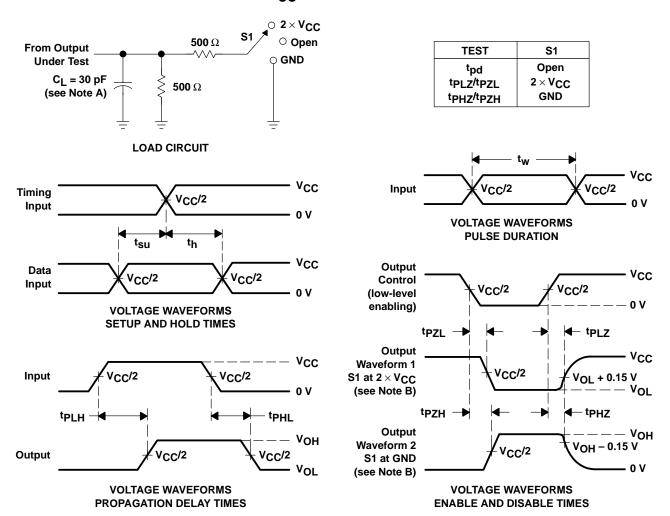
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- tpZL and tpZH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.5 V \pm 0.2 V

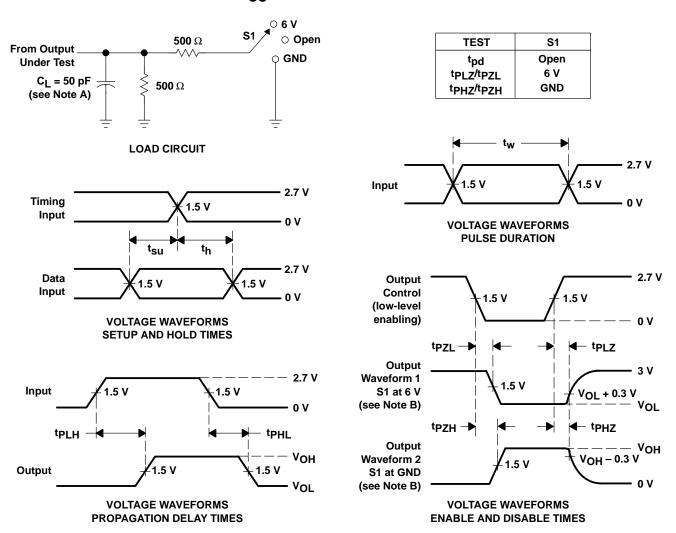


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpz and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{Q} = 50 Ω , $t_{f} \leq$ 2.5 ns, $t_{f} \leq$ 2.5 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

